Microsemi POWER PRODUCTS GROUP

Power **MOS8** Cooler!

**1000V, 32A, 0.38Ω Max**

N-Channel MOSFET

Power MOS 8™ is a high speed, high voltage N-channel switch-mode power MOSFET. A proprietary planar stripe design yields excellent reliability and manufacturability. Low switching loss is achieved with low input capacitance and ultra low C_{rss} "Miller" capacitance. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control slew rates during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency. Reliability in flyback, boost, forward, and other circuits is enhanced by the high avalanche energy capability.

T-Max™   TO-264
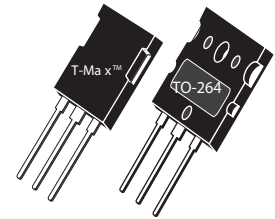
APT31M100B2   **APT31M100L**

Single die MOSFET
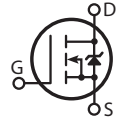
FEATURES

- **Fast switching with low EMI/RFI**
- **Low $R_{DS(on)}$**
- **Ultra low C_{rss} for improved noise immunity**
- **Low gate charge**
- **Avalanche energy rated**
- **RoHS compliant**

TYPICAL APPLICATIONS

- **PFC and other boost converter**
- **Buck converter**
- **Two switch forward (asymmetrical bridge)**
- **Single switch forward**
- **Flyback**
- **Inverters**

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
I_D	Continuous Drain Current @ T_C = 25°C	32	A
	Continuous Drain Current @ T_C = 100°C	20	
I_{DM}	Pulsed Drain Current ①	120	
V_{GS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy ②	1875	mJ
I_{AR}	Avalanche Current, Repetitive or Non-Repetitive	16	A

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
P_D	Total Power Dissipation @ T_C = 25°C			1040	W
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.12	°C/W
$R_{\theta CS}$	Case to Sink Thermal Resistance, Flat, Greased Surface		0.11		
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55		150	°C
T_L	Soldering Temperature for 10 Seconds (1.6mm from case)			300	
W_T	Package Weight		0.22		oz
			6.2		g
Torque	Mounting Torque (TO-264 Package), 4-40 or M3 screw			10	in·lbf
				1.1	N·m

050-8071   Rev D   7-2011

Static Characteristics T_J = 25°C unless otherwise specified   APT31M100B2_L

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250µA		1000			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D = 250µA			1.15		V/°C
$R_{DS(on)}$	Drain-Source On Resistance ③	V_{GS} = 10V, I_D = 16A			0.34	0.38	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 2.5mA		3	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient				-10		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 1000V	T_J = 25°C			100	µA
		V_{GS} = 0V	T_J = 125°C			500	
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V				±100	nA

Dynamic Characteristics T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g_{fs}	Forward Transconductance	V_{DS} = 50V, I_D = 16A		34		S
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V f = 1MHz		8500		pF
C_{rss}	Reverse Transfer Capacitance			115		
C_{oss}	Output Capacitance			700		
$C_{o(cr)}$ ④	Effective Output Capacitance, Charge Related	V_{GS} = 0V, V_{DS} = 0V to 667V		290		
$C_{o(er)}$ ⑤	Effective Output Capacitance, Energy Related			150		
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, I_D = 16A, V_{DS} = 500V		260		nC
Q_{gs}	Gate-Source Charge			46		
Q_{gd}	Gate-Drain Charge			125		
$t_{d(on)}$	Turn-On Delay Time	**Resistive Switching** V_{DD} = 667V, I_D = 16A R_G = 2.2Ω⑥, V_{GG} = 15V		39		ns
t_r	Current Rise Time			35		
$t_{d(off)}$	Turn-Off Delay Time			130		
t_f	Current Fall Time			33		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode)			32	A
I_{SM}	Pulsed Source Current (Body Diode)①				120	
V_{SD}	Diode Forward Voltage	I_{SD} = 16A, T_J = 25°C, V_{GS} = 0V			1	V
t_{rr}	Reverse Recovery Time	I_{SD} = 16A③		1140		ns
Q_{rr}	Reverse Recovery Charge	di_{SD}/dt = 100A/µs, T_J = 25°C		30		µC
dv/dt	Peak Recovery dv/dt	I_{SD} ≤ 16A, di/dt ≤1000A/µs, V_{DD} = 667V, T_J = 125°C			10	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at T_J = 25°C, L = 14.65mH, R_G = 2.2Ω, I_{AS} = 16A.

③ Pulse test: Pulse Width < 380µs, duty cycle < 2%.

④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$.

⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$. To calculate $C_{o(cr)}$ for any value of V_{DS} less than $V_{(BR)DSS}$, use this equation: $C_{o(er)}$ = -2.47E-7/V_{DS}^2 + 4.36E-8/V_{DS} + 8.44E-11.

⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

Microsemi reserves the right to change, without notice, the specifications and information contained herein.
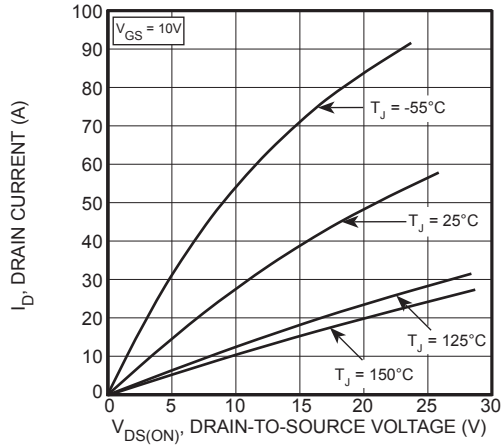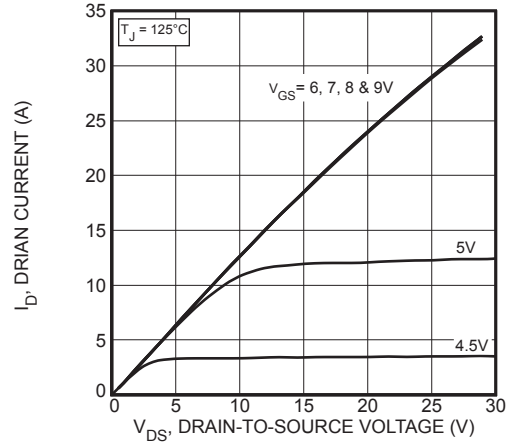
Figure 1, Output Characteristics
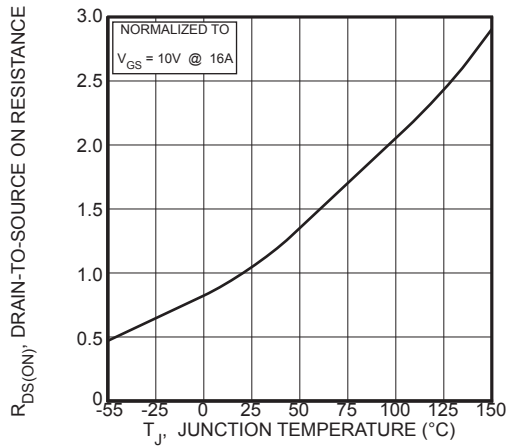

Figure 2, Output Characteristics

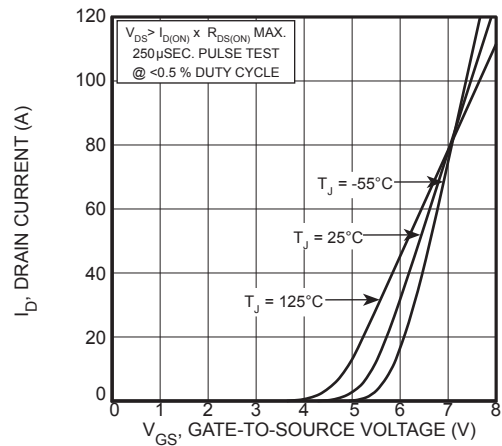**Figure 3, R_DS(ON) vs Junction Temperature**

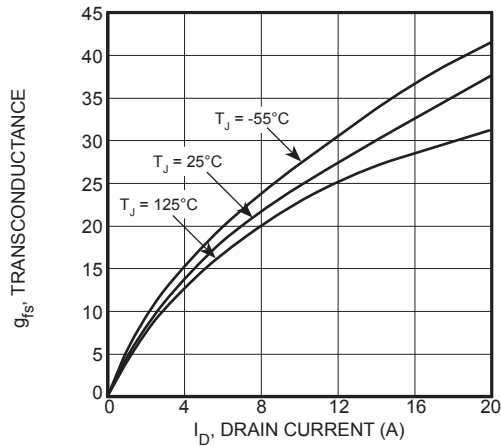**Figure 4, Transfer Characteristics**
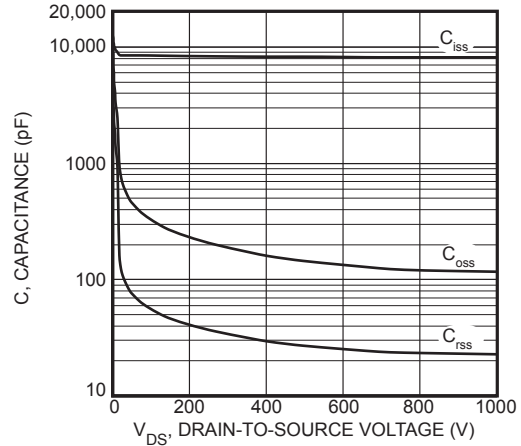

Figure 5, Gain vs Drain Current
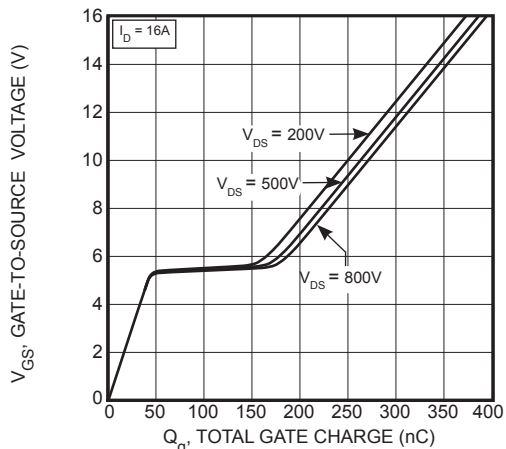

Figure 6, Capacitance vs Drain-to-Source Voltage

Figure 7, Gate Charge vs Gate-to-Source Voltage

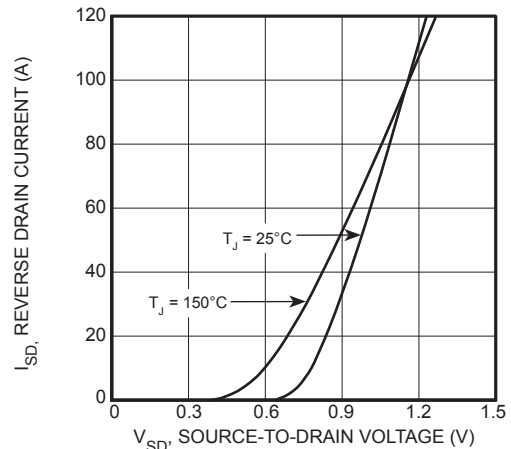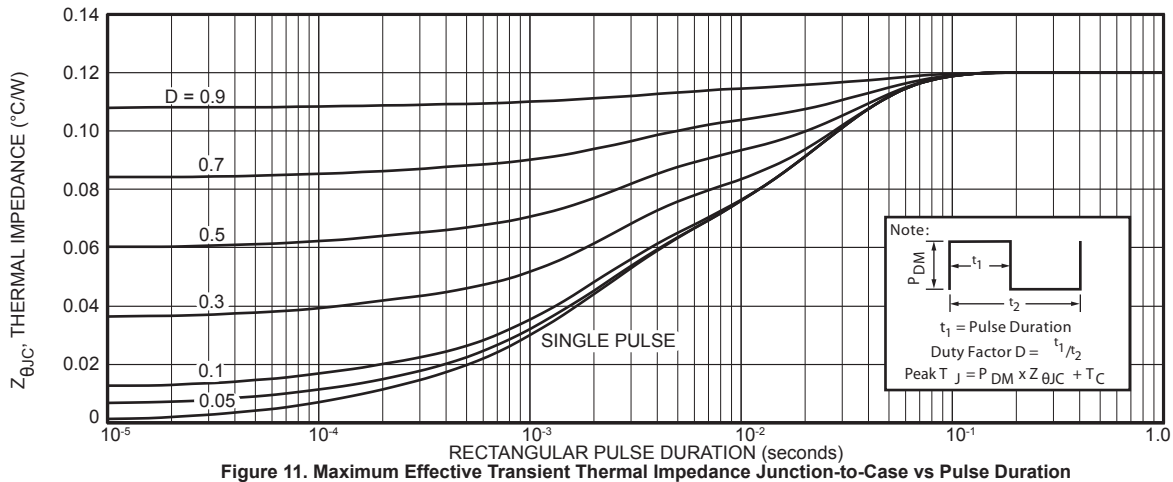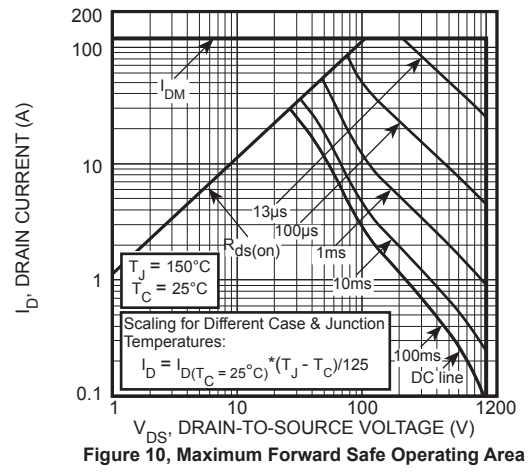**Figure 8, Reverse Drain Current vs Source-to-Drain Voltage**

Figure 9, Forward Safe Operating Area

Figure 10, Maximum Forward Safe Operating Area

Scaling for Different Case & Junction Temperatures:

$$I_D = I_{D(T_C = 25°C)} {}^*(T_J - T_C)/125$$

Note:

t_1 = Pulse Duration

Duty Factor D = t_1/t_2

Peak $T_J = P_{DM} \times Z_{\theta JC} + T_C$

Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration
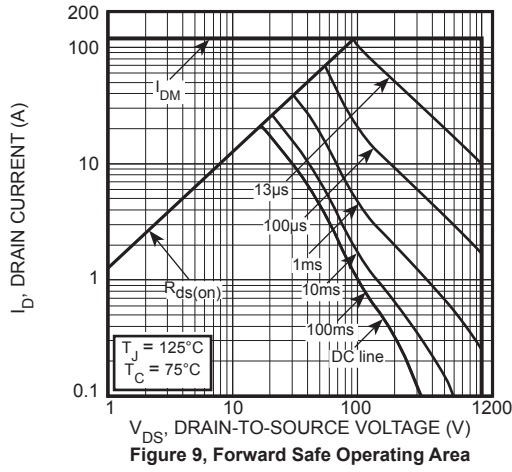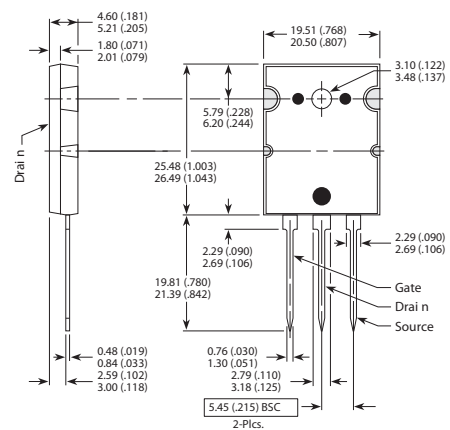
T-MAX™ (B2) Package Outline

(e3) 100% Sn Plated
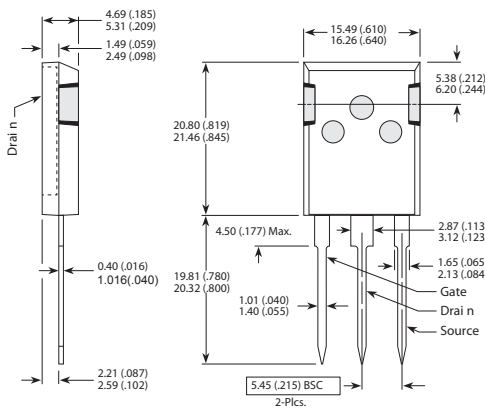
These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters (Inches)

TO-264 (L) Package Outline

Dimensions in Millimeters (Inches)

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